

Trapping characteristics and a donor-complex (DX) model for persistent-photoconductivity trapping center in Te-doped

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#	ARTICLE	IF	CITATIONS
1	Study of intensity pulsations in proton- α -bombarded stripe- α -geometry double- α -heterostructure $\text{Al}_x\text{Ga}_{1-x}\text{As}$ lasers. Journal of Applied Physics, 1979, 50, 4620-4637.	1.1	68
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